SEP 2 4 2003 SEP 2

PTO/SB/21 (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Properwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

10/605,005

Applicati n Number

TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

Filing Date	08/31/2003			
First Named Inventor	Chien-Sheng Yang			
Group Art Unit		<u> </u>		
Examiner Name				

Total Number of Pages in This Submission 3 Attorney Docket Number AUOP0008USA

		ENCLOSURES (check all that apply)			
Extension of Time F Express Abandonm Information Disclos Certified Copy of Pr Document(s) Response to Missin Incomplete Application Response to	ed ly eclaration(s) Request ment Request sure Statement riority ng Parts/	Assignment Papers (for an Application) Drawing(s) Licensing-related Papers Petition Petition to Convert to a Provisional Application Power of Attorney, Revocation Change of Correspondence Address Terminal Disclaimer Request for Refund CD, Number of CD(s) After Allowance Communication to Group Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Other Enclosure(s) (please identify below): CD, Number of CD(s) Remarks			
Firm		JRE OF APPLICANT, ATTORNEY, OR AGENT			
or Individual name	Winston Hsu, F	Reg. No.: 41,526			
Signature	Weiston Her				
Date	9/23/2003				
CERTIFICATE OF MAILING					
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class					

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.

Date

mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231 on this date:

Typed or printed name

Signature

SEP 2 4 2013 13 14 OF PAPER THE PAPER WORK F

Approved for use through 04/30/2003. OMB 0651-0032
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

FEE TRANSMITTAL for FY 2003

Effective 01/01/2003. Patent fees are subject to annual revision.

Applicant claims small entity status. See 37 CFR 1.27

Winston Hsu

Name (Print/Type)

Signature

TOTAL AMOUNT OF PAYMENT

(\$)	0.00
------	------

Complete if Known			
Application Number	10/605,005		
Filing Date	08/31/2003		
First Named Inventor	Chien-Sheng Yang		
Examiner Name			
Art Unit			
Attorney Docket No.	ALIOPODRUSA		

METHOD OF PAYMENT (check all that apply)				FE	E CALCULATION (continued)	
Check Credit card Money Other None	3. A	DDIT	IONA	L FE	ES	
Deposit Account:		Entity				
Deposit FO 0004	Fee Code	Fee (\$)	Fee Code	Fee	Fee Description	
Account Number 50-0801	1051	(' '	2051	(\$) 65		Fee Paid
Deposit Account North America International Patent Office	1052	_	2052	25	Surcharge - late filing fee or oath Surcharge - late provisional filing fee or	
Name ————————————————————————————————————			2002	25	cover sheet	<u> </u>
The Commissioner is authorized to: (check all that apply)	1053		1053	130	3	
Charge fee(s) indicated below Credit any overpayments		2,520	i .		For filing a request for ex parte reexamination	
Charge any additional fee(s) during the pendency of this application	1804	920*	1804	920*	Requesting publication of SIR prior to Examiner action	
Charge fee(s) indicated below, except for the filing fee to the above-identified deposit account.	1805	1,840*	1805	1,840*	Requesting publication of SIR after Examiner action	
FEE CALCULATION	1251	110	2251	5 5	Extension for reply within first month	
1. BASIC FILING FEE	1252	410	2252	205	Extension for reply within second month	
Large Entity Small Entity Fee Fee Fee Fee Fee Description Fee Paid	1253		2253	465	Extension for reply within third month	
Code (\$) Code (\$)	1254	1,450	2254	725	Extension for reply within fourth month	
1001 750 2001 375 Utility filing fee	1255	1,970	2255	985	Extension for reply within fifth month	
1002 330 2002 165 Design filing fee	1401	320	2401	160	Notice of Appeal	
1003 520 2003 260 Plant filing fee	1402	320	2402	160	Filing a brief in support of an appeal	
1004 750 2004 375 Reissue filing fee	1403	280	2403		Request for oral hearing	
1005 160 2005 80 Provisional filing fee		1,510	1451	1,510	Petition to institute a public use proceeding	
SUBTOTAL (1) (\$) 0.00	1452	110	2452	55	Petition to revive - unavoidable	
2. EXTRA CLAIM FEES FOR UTILITY AND REISSUE		1,300	2453	650	Petition to revive - unintentional	
Fee from Ext <u>ra Claims below</u> Fee Paid	1501	1,300	2501		Utility issue fee (or reissue)	
Total Claims X = X		470	2502		Design issue fee	
Independent Claims - 3** = X = =	1503 1460	630 130	2503		Plant issue fee	
Multiple Dependent	1807	50	1460		Petitions to the Commissioner	
Large Entity Small Entity	1806	180	1807	_	Processing fee under 37 CFR 1.17(q)	
Fee Fee Fee <u>Fee Description</u> Code (\$)			1806		Submission of Information Disclosure Stmt	
1202 18 2202 9 Claims in excess of 20	8021	40	8021	40	Recording each patent assignment per property (times number of properties)	
1201 84 2201 42 Independent claims in excess of 3	1809	750	2809	375	Filing a submission after final rejection (37 CFR 1.129(a))	
1203 280 2203 140 Multiple dependent claim, if not paid	1810	750	2810		For each additional invention to be	
1204 84 2204 42 ** Reissue independent claims					examined (37 CFR 1.129(b))	
over original patent 1205 18 2205 9 ** Reissue claims in excess of 20	1801	750	2801	375	Request for Continued Examination (RCE)	
1205 18 2205 9 ** Reissue claims in excess of 20 and over original patent	1802	900	1802	900	Request for expedited examination of a design application	
SUBTOTAL (2) (\$) 0.00		ee (spe				
**or number previously paid, if greater; For Reissues, see above	*Reduc	ced by E	Basic Fi	iling Fe	e Paid SUBTOTAL (3) (\$) 0.00	
SUBMITTED BY					(Complete (if applicable)	

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

This collection of information is required by 37 CFR 1.17 and 1.27. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Commissioner for Patents, Washington, DC 20231.

Registration No.

(Attorney/Agent)

41,526

Telephone 886289237350

Date



PTO/SB/02B (11-00)
Approved for use through 10/31/2002. OMB 0651-0032
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

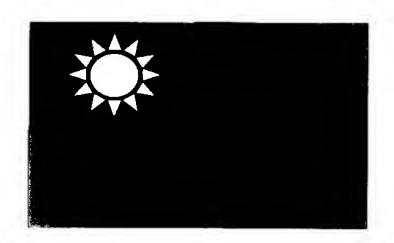
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

DECLARATION — Supplemental Priority Data Sheet

Additional foreign applications:					
Prior Foreign Application Number(s)	Country	Foreign Filing Date (MM/DD/YYYY)	Priority Not Claimed	Certified Copy Attached? YES NO	
092119572	Taiwan R.O.C	07/17/2003			

Burden Hour Statement: This form is estimated to take 21 minutes to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.





यित विश्व विश्व

中華民國經濟部智慧財產局。

INTELLECTUAL PROPERTY OFFICE MINISTRY OF ECONOMIC AFFAIRS REPUBLIC OF CHINA

茲證明所附文件,係本局存檔中原申請案的副本,正確無訛,其申請資料如下:

This is to certify that annexed is a true copy from the records of this office of the application as originally filed which is identified hereunder:

申 請 日: 西元 2003 年 07 月 17 日 Application Date

申 請 案 號: 092119572

Application No.

인도 인도 인도 인도 인도

52

5252

申 請 人: 友達光電股份有限公司

Applicant(s)

局 長 Director General

祭練生

發文日期: 西元 2003 年 8 月 26 日

Issue Date

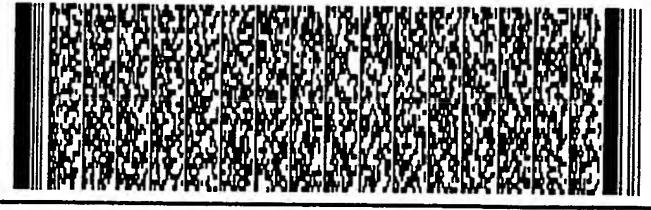
發文字號: 09220854900

Serial No.



申請日期:	IPC分類	
申請案號:		

<u> </u>		
(以上各欄	由本局填	發明專利說明書
	中文	具可變電阻之光學式指紋感測器
發明名稱	英 文	OPTICAL FINGERPRINT SENSOR WITH VARIABLE RESISTORS
	姓 名 (中文)	1. 楊健生
-	姓 名 (英文)	1. Yang, Chien-Sheng
發明人(共1人)	國 籍 (中英文)	1. 中華民國 TW
	住居所 (中 文)	1. 台北市民生東路四段九十七巷四弄二十五號
	住居所 (英 文)	1. No. 25, Alley 4, Lane 97, Sec. 4, Min-Sheng E. Rd., Taipei City, Taiwan R.O.C.
	名稱或 姓 名 (中文)	1. 友達光電股份有限公司
	名稱或 姓 名 (英文)	1. AU Optronics Corp.
゠	國 籍 (中英文)	1. 中華民國 TW
申請人(共1人)	住居所 (營業所) (中 文)	1. 新竹市新竹科學工業園區力行二路一號 (本地址與前向貴局申請者相同)
	住居所 (營業所) (英 文)	1. No. 1, Li-Hsin Road 2, Science-Based Industrial Park Hsin-Chu City, Taiwan, R.O.C.
	代表人(中文)	1.李焜耀
	代表人(英文)	Lee, Kuen-Yao
HIII PACATIZATU	NATIVY JOYNA	パンル ドング・ルタイトは み・ログノフト 第一日 アン・ス・コンドル・ 第二日



四、中文發明摘要 (發明名稱:具可變電阻之光學式指紋感測器)

五、(一)、本案代表圖為:第 五 圖 (二)、本案代表圖之元件代表符號簡單說明

40 辨識單元

42 第一參考電壓端

44 第二參考電壓端

46 啟動端

六、英文發明摘要 (發明名稱:OPTICAL FINGERPRINT SENSOR WITH VARIABLE RESISTORS)

A fingerprint sensor for sensing a fingerprint has a detecting and processing circuit and a plurality of sensing units. Each of the sensing units has a switch element, a first resister, and a second resister. The switch element has a first terminal, a second terminal, and a third terminal. Resistance of the second resister is fixed. The fingerprint influences intensity of





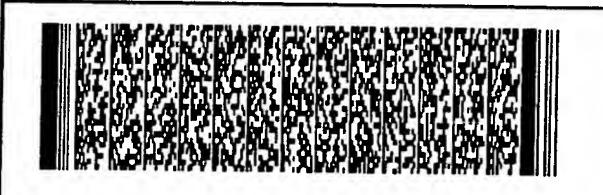
四、中文發明摘要 (發明名稱:具可變電阻之光學式指紋感測器)

48 輸出端

56 電晶體

六、英文發明摘要 (發明名稱:OPTICAL FINGERPRINT SENSOR WITH VARIABLE RESISTORS)

light illuminating the first resister so that resistance of the first resister and a voltage level of the second terminal change. When the switch elements are turned on, the detecting and processing circuit analyzes the fingerprint according to the voltage levels of the second terminals of the plurality switch elements.



一、本案已向			
國家(地區)申請專利	申請日期	案號	主張專利法第二十四條第一項優先
	• • • • • • • • • • • • • • • • • • • •		
		無	
二、□主張專利法第二十	五條之一第一項優	: 先權:	
申請案號:			
下明示功6.		無	
日期:			
三、主張本案係符合專利:	法第二十條第一項	□第一款但書或	成□第二款但書規定之期間
日期:			
中州 :		•	
四、□有關微生物已寄存法	於國外:		
寄存國家:		益	
寄存機構:		無	
寄存日期: 寄存號碼:			
可行號啊. □有關微生物已寄存者	炒圈內(木吕昕 华台	マッ 欠方 機構)・	
寄存機構:	人因门(本河川祖及	C~可行戏件儿.	
寄存日期:		無	
寄存號碼:			
□熟習該項技術者易力	於獲得,不須寄存。	•	
EX-POLICING COMPANY CHARACTER			

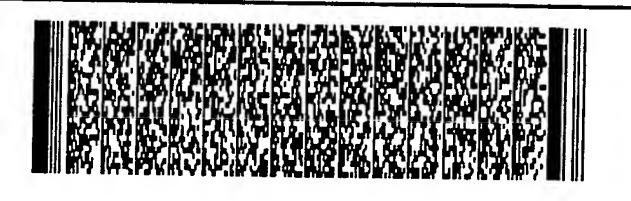
五、發明說明 (1)

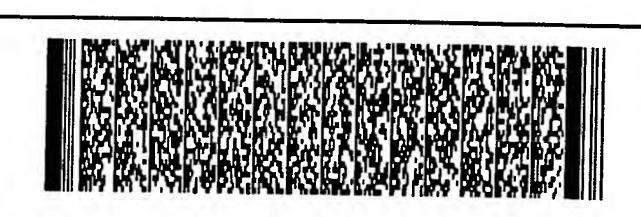
發明所屬之技術領域

本發明係概括關於一指紋感測器,尤指一種具可變電阻之光學式指紋感測器。

先前技術

請參考圖二,圖二為圖一感應區 14的電路圖。感應區 14 包含有複數個排列成矩陣的辨識單元 16,每一辨識單元 16皆是用來感應使用者之指紋上對應位置上的紋路,並分別包含有一電晶體 18以及一偵測電容 Cf。當感應區 14 使時,電晶體 18的源極 S會被施予一偵測訊號 Vs1或 Vs2,而當使用者的指紋按壓於感應區 14的表面時,偵測





五、發明說明 (2)

電容 Cf的 電容值會改變。當偵測電容 Cf的電容值改變時,電晶體 18的 閘極電壓即會因電容藕合效應而改變,其中電晶體 18閘極電壓的改變量 Δ Vg係由偵測電容 Cf的電容值所決定,並可以以下列方程式表示:

 $\Delta Vg = Vs \cdot Cgs / (Cgs + Cf)$

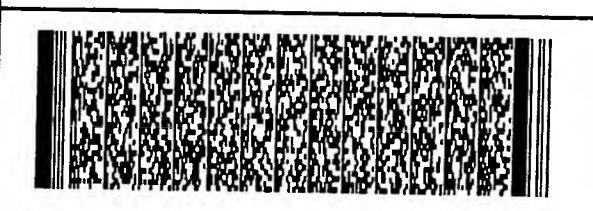
其中,VS為偵測訊號 VS1或 VS2的電壓值; CgS為電晶體 18之閘極 G與源極 S之間的寄生電容值;而 Cf則為偵測電容的電容值。

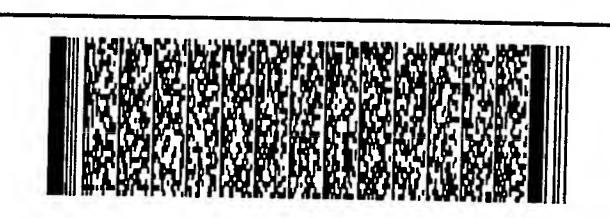
電晶體 18的 開極電壓的變化量 Δ V g 會直接影響流經電晶體 18的電流 I之大小,而辨識單元外部訊號偵測處理電路 12即是依據電流 I的變化情形來辨識出使用者的指紋。然而,這種藉由偵測流經電晶體 18的電流 I之變化來辨識指紋的方法,其靈敏度易受到相鄰電晶體 18之漏電流的影響,而使得其辨識的準確度無法有效地提高。

發明內容

因此,本發明的目的即在於提供一種藉由偵測電位之變化來辨識指紋的指紋感測器,以解決上述的問題。

依據本發明實施的指紋感測器包含有一辨識單元外部訊

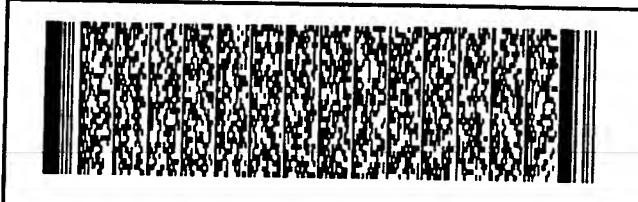


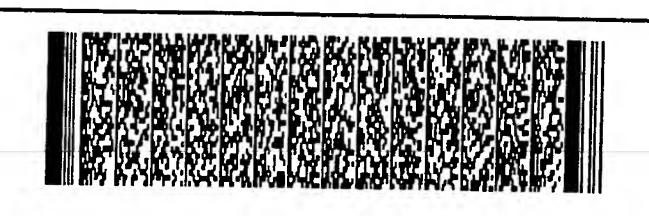


五、發明說明 (3)

實施方式

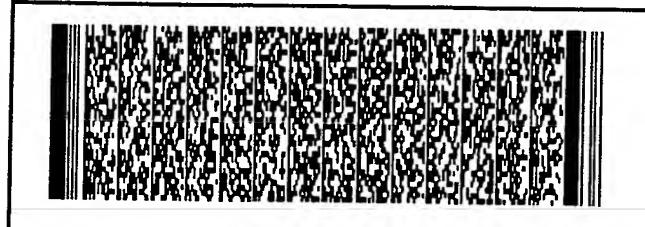
請參考圖三,圖三為本發明電阻式指紋感測器 50之功能 方塊圖。指紋感測器 50為一種電阻式指紋感測器 (resistive fingerprint sensor),其係藉由偵測因電 阻值變化而改變的電壓值來辨識指紋感測器 50包 含有一辨識單元外部訊號偵測處理電路 52以及一戶 54。感應區 54內包含有複數個辨識單元,而每一辨 54。感應區 54內包含有複數個辨識單元,而每 54。感應區 54內包含有複數個辨識單元,而每 54。感應區 54內包含有複數個辨識單元,而每 54。感應區 54內包含有複數個辨識單元,而每 54。感應區 54內包含有複數個辨識單元,而每 54。於應區 54內包含有複數個辨識單元,而每 54。於應區 54內包含有複數個辨識單元,而 54。於應區 54內包含有複數個辨識單元,而 54。於應區 54內包含有複數個辨證單元,而 54。於實際

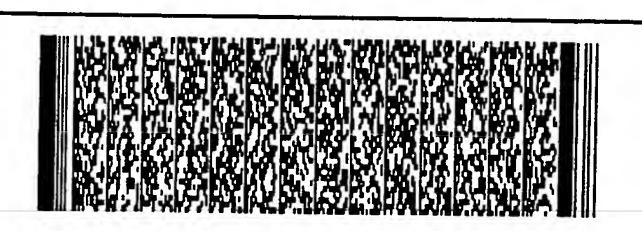




五、發明說明 (4)

請多者 40 m 电 44 m 44 m 电 44 m 4





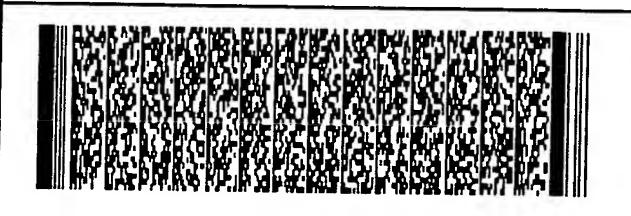
五、發明說明 (5)

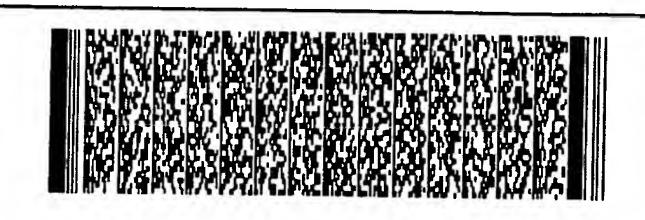
而改變,而第二電阻 R2可由氧化銦錫 (indium tin oxide, ITO) 製成。在本實施例中,電晶體 56為一金屬氧化半導體 (MOS)電晶體,其包含有一為閘極 (gate)的第二端 G、一為源極 (source)的第二端,以及一為汲極 (drain)的第三端。每一電晶體 56之 閘極 G連接於一對應的啟動端 46,啟動端 46可控制電晶體 56的導通與否。一般情況下,啟動端 46條處於浮接的狀態時,且電晶體 56是不導通的,然而當啟動端 46被施予一啟動電壓 Vs1、Vs2、Vs3或 Vs4時,電晶體 56內則會形成一通道,而使得源極 S與汲極 D之間呈導通的狀態。除此之外,電晶體 56的源極 S連接於第一電阻 R1與第二電阻 R2,而其汲極 D則連接於一對應的輸出端 48。

當透光材質 60放置於感應區 54上,以對指紋 62進行感測時,一第一參考電壓 Vrefl會被施加於第一參考電壓端 42,而一第二參考電壓 Vref2會被施加於第二參考電壓端 44,其中第一參考電壓 Vref1的電壓值會異於第二參考電壓 Vref2的電壓值。因此,電晶體 56之源極 S的電位 Vs可以以下列方程式表示:

$$Vs = Vref1 - \left[\frac{r1}{r1 + r2}(Vref1 - Vref2)\right] = Vref2 - \left[\frac{r2}{r1 + r2}(Vref2 - Vref1)\right]$$

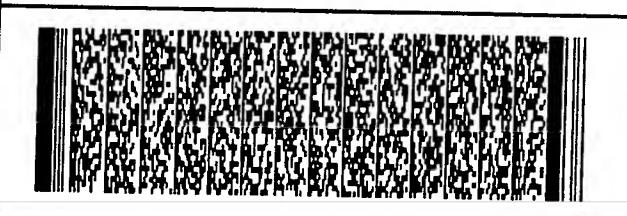
其中, r1為第一電阻 R1之電阻值, r2為第二電阻 R2之電阻值。

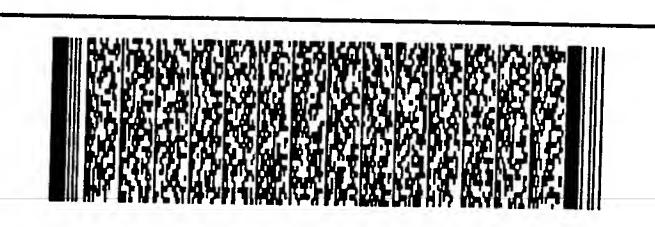




五、發明說明 (6)

當各電晶體 56之源極 S的電位 V S因指紋 62的遮蔽而改變後,辨識單元外部訊號偵測處理電路 52即會藉由各啟動端 46施加一啟動電壓 V S1、 V S2、 V S3或 V S4至各電晶體 56之閘極 G,以使對應的電晶體 56導通。當電晶體 56導通後,導通的電晶體 56之汲極 D的電位即會受到源極 S電位的影響而改變。因此,在導通狀態下的電晶體 56之汲極 D電位亦可反映出指紋 62之條紋的排列情形。此外,辨識



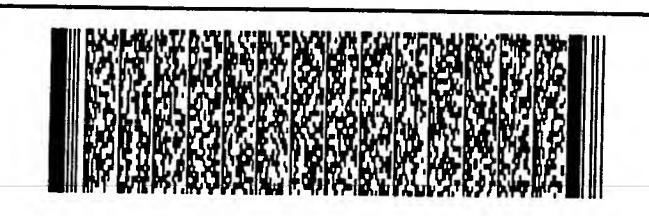


五、發明說明 (7)

單元外部訊號偵測處理電路 52可藉由輸出端 48來量測出 汲極 D的電位,之後再依據所量測的汲極 D電位來分析指 紋 62的條紋排列情形,以達到辨識指紋 62的目的。需說 明的是,未避免各電晶體 56的汲極 D電位相互干擾,同一 時間內,只有單一列的電晶體 56之閘極 G會被施予上述的 啟動電壓。

以上所述僅為本發明之較佳實施例,凡依本發明申請專利範圍所做之均等變化與修飾,皆應屬本發明專利之涵蓋範圍。





圖式簡單說明

圖式之簡單說明

圖一為習知電容式指紋感測器之功能方塊圖。

圖二為圖一指紋感測器之一感應區的電路圖。

圖三為本發明電阻式指紋感測器之功能方塊圖。

圖四為利用圖三指紋感測器辨識一指紋時之示意圖。

圖五為圖三感應區之電路圖。

圖式之符號說明

10、50 指紋感測器

12、52 辨識單元外部訊號偵測處理電路

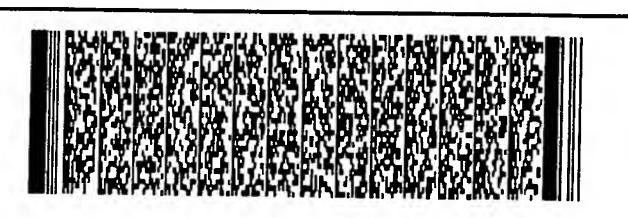
14、54 感應區 16、40 辨識單元

18、56 電晶體 42 第一參考電壓端

44 第二參考電壓端 46 啟動端

48 輸出端 60 透光材質

62 指紋 64 光線

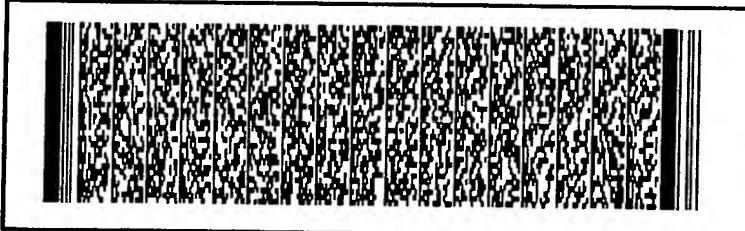


六、申請專利範圍

- 1.一種指紋感測器,用來辨識一指紋,該指紋感測器包含有:
- 一辨識單元外部訊號偵測處理電路;以及
- 複數個辨識單元,每一辨識單元分別包含有:
- 一開關元件,其包含有一第一端、一第二端以及一第三端,該第一端連接於一啟動端,該第三端連接於該辨識單元外部訊號偵測處理電路,而該啟動端係用來控制該開關元件之開啟及關閉;
- 一第一電阻,其一端連接於上述開關元件之第二端,該指紋會影響該第一電阻所受光照之強度,而使該第一電阻之電阻值改變,進而使該第二端之電位改變;以及一第二電阻,其一端連接於上述開關元件之第二端,且其具有一固定的電阻值;

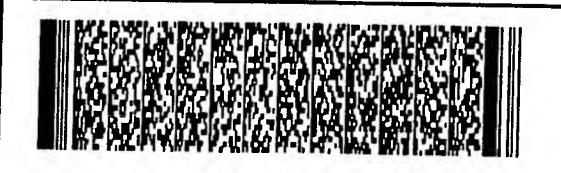
其中當該等開關元件開啟時,該辨識單元外部訊號偵測處理電路會依據該等開關元件之第二端的電位來辨識該指紋。

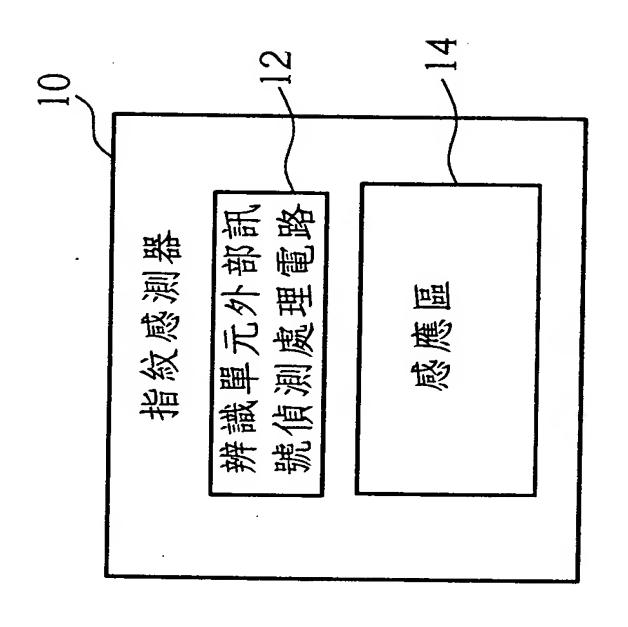
2.如申請專利範圍第1項之指紋感測器,其中每一辨識單元第一電阻之一端皆電連接於一第一參考電壓端,且每一辨識單元第二電阻之一端皆電連接於一第二參考電壓端,一第一參考電壓施加於該第一參考電壓端,一第二參考電壓施加於該第二參考電壓端,而該第一參考電壓 之電壓值係異於該第二參考電壓之電壓值。

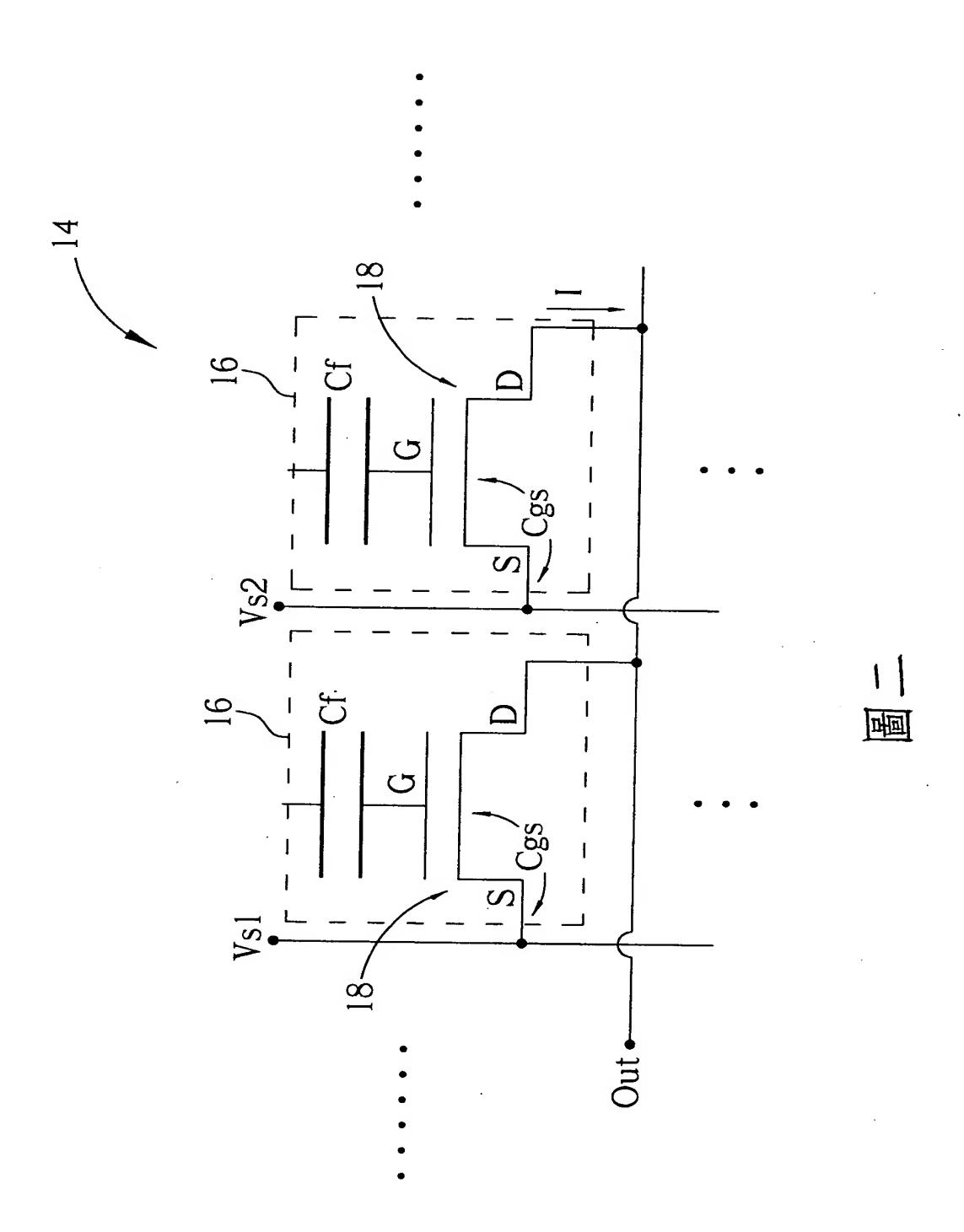


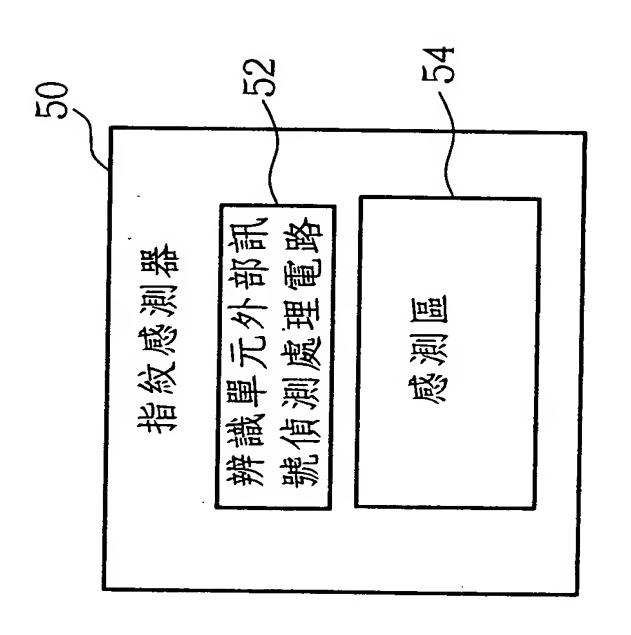
六、申請專利範圍

- 3.如申請專利範圍第1項之指紋感測器,其中每一開關元件皆為一電晶體。
- 4.如申請專利範圍第1項之指紋感測器,其中該第一電阻係由非晶矽 (amorphous silicon)製成。
- 5.如申請專利範圍第1項之指紋感測器,其中該第二電阻係由氧化銦錫 (indium tin oxide, ITO)製成。

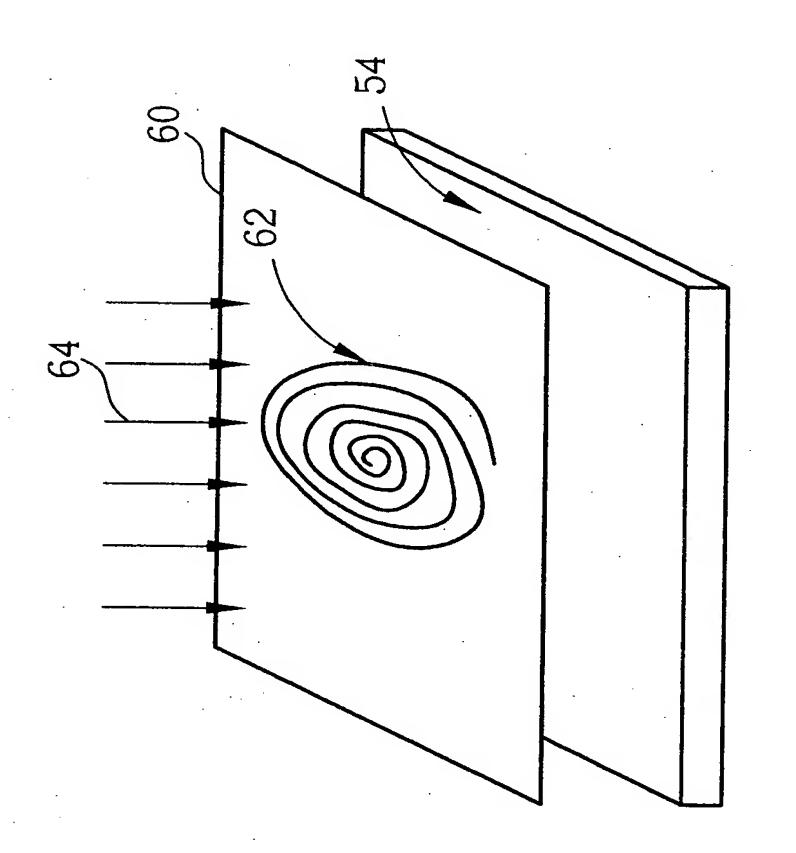








上



.

圖四

